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Silicon 4 6 4transistor in a TO-252 Plastic Package.

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@ ƒ Parameter	… Z Symbol	ƒ › Rating	% y Unit
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	80	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	8.0	A
Collector Peak Current	I_{CM}	16.0	A
Collector Power Dissipation	P_D(T_A=25 -)	1.75	W
Collector Power Dissipation	P_D(T_C=25 -)	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

@ ƒ Parameter	… Z Symbol	y ¡ Ú ^ Test Conditions	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
Collector to Emitter Breakdown Voltage	[redacted]	[redacted]	[redacted]	[redacted]	[redacted]	[redacted]
Collector Cut-Off Current	I_{CES}	V_{CE}= 80V V_{BE}= 0				

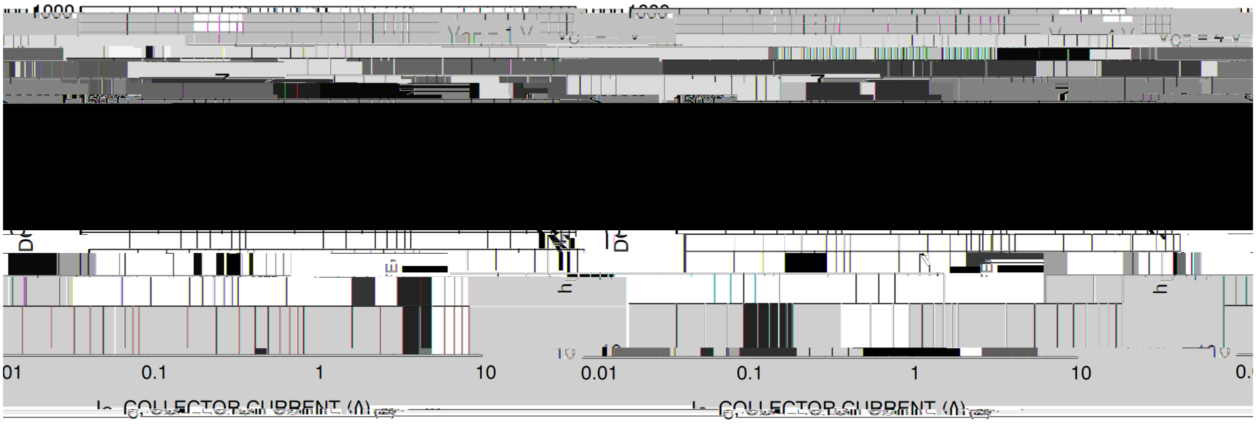
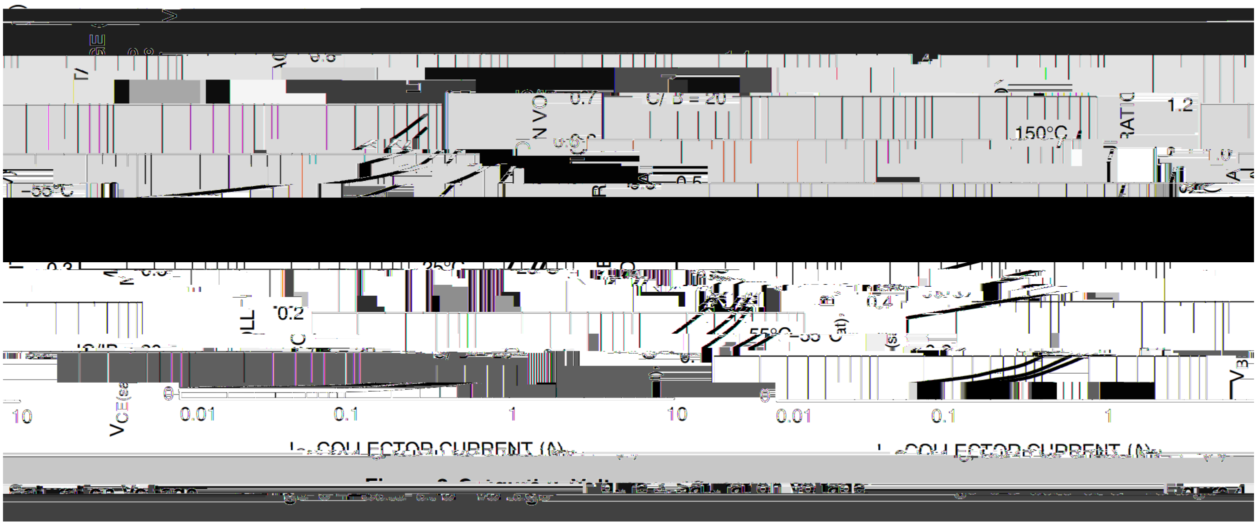
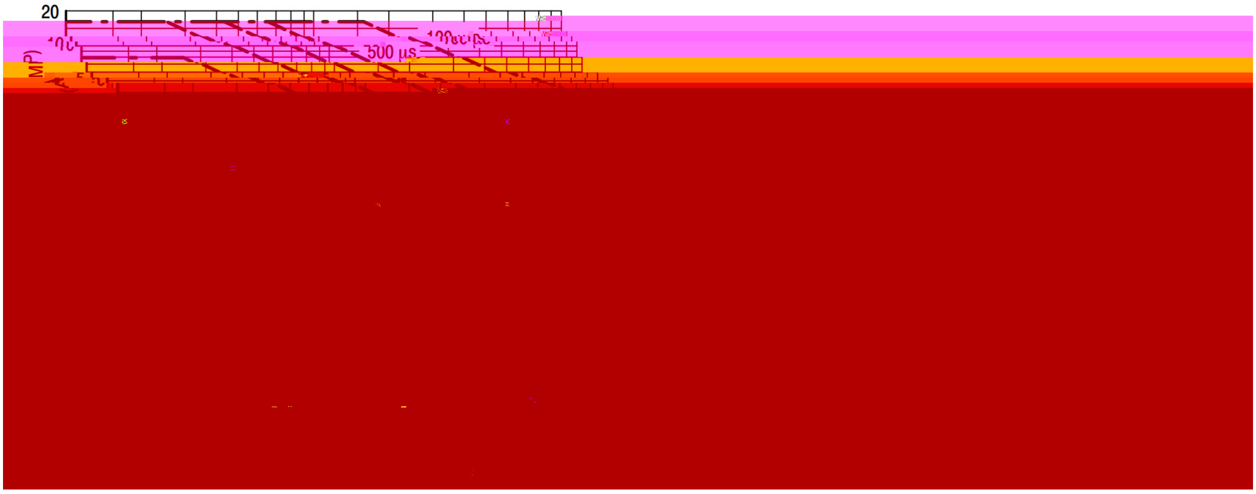


Figure 1. DC Current Gain　　**Figure 2. DC Current Gain**





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单位：mm

Symbol	Min	Max	Symbol	Min	Max
A	2.20	2.40	E	5.95	6.25
[illegible]	[illegible]	[illegible]	[illegible]	[illegible]	[illegible]
b	0.50	0.90	e2	4.43	4.73
b1	0.45	0.55	L1	9.45	9.95
[illegible]	[illegible]	[illegible]	L2	[illegible]	[illegible]
D	6.45	6.75	[illegible]	[illegible]	[illegible]
D1	5.10	5.50	K	0.00	[illegible]

TO-252

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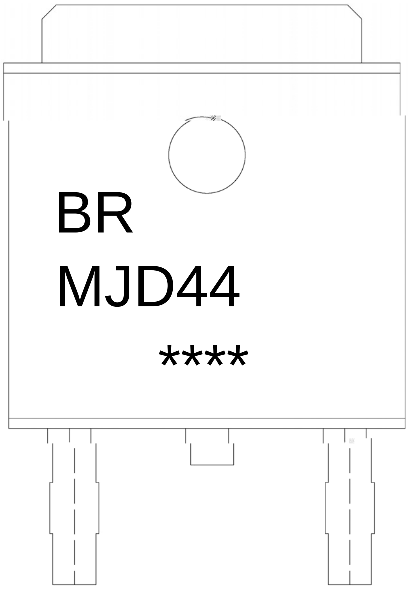

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BR y ¸ [W A

3 0 * y º Z W A

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Note:

BR:	Company Code
MJD44:	Product Type Code
****:	Lot No. Code, code change with Lot No